

Maximum Ratings (@T_A = +25 °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	650	V
Gate-Source Voltage			V_{GSS}	±30	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	$T_C = +25 ^{\circ}$ C $T_C = +70 ^{\circ}$ C	I _D	9.0 7.0	А
Pulsed Drain Current (Note 6) 10us pulse, pulse duty cycle<=1%			I _{DM}	30	Α
Avalanche Current (Note 7) V _{DD} = 100V, V _{GS} = 10V, L = 60mH			I _{AR}	2.7	Α
Repetitive Avalanche Energy (Note 7) $V_{DD} = 100V$, $V_{GS} = 10V$, $L = 60mH$			E _{AR}	260	mJ

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5) $T_C = +25 ^{\circ}C$ $T_C = +70 ^{\circ}C$	P _D	165 100	W
Thermal Resistance, Junction to Case (Note 5)	$R_{\theta JC}$	0.7	.c∖M
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

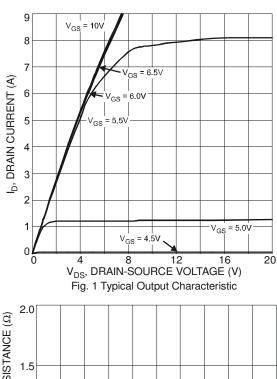
Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

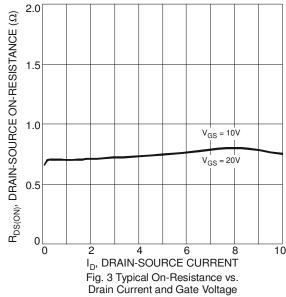
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	OFF CHARACTERISTICS (Note 8)					
Drain-Source Breakdown Voltage	BV _{DSS}	650	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25 °C	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 650V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	3	_	5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	R _{DS} (ON)	_	0.7	1.3	Ω	$V_{GS} = 10V, I_D = 4.5A$
Forward Transfer Admittance	Y _{fs}	_	8.5	_	S	$V_{DS} = 40V, I_{D} = 4.5A$
Diode Forward Voltage	V_{SD}	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	2,310	_	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	Coss	_	122	_		
Reverse Transfer Capacitance	C _{rss}	_	2.2	_		
Gate Resistance	R_g	_	2.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge V _{GS} = 10V	Q_g	_	39	_	nC	$V_{GS} = 10V, V_{DS} = 520V,$ $I_{D} = 8A$
Gate-Source Charge	Q_{gs}	_	8.5	_		
Gate-Drain Charge	Q_{gd}	_	11.9	_		
Turn-On Delay Time	t _{D(on)}	_	39	_	ns	
Turn-On Rise Time	t _r	_	29	_	ns	$V_{GS} = 10V, V_{DS} = 325V,$
Turn-Off Delay Time	t _{D(off)}		122	_	ns	$R_G = 25\Omega$, $I_D = 8A$
Turn-Off Fall Time	t _f	_	28	_	ns	
Body Diode Reverse Recovery Time	t _{rr}	_	570	_	ns	$dI/dt = 100A/\mu s$, $V_{DS} = 100V$,
Body Diode Reverse Recovery Charge	Q_{rr}	_	4.17	_	μC	$I_F = 8A$

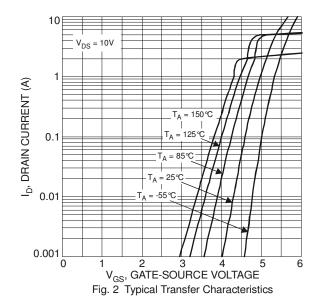
Notes:

- 5. Device mounted on an infinite heatsink.6. Repetitive rating, pulse width limited by junction temperature.
- 7. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = +25 °C.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to production testing.









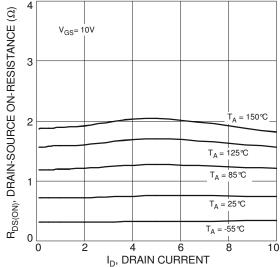
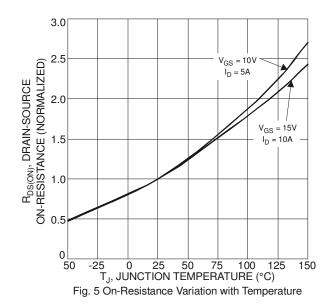
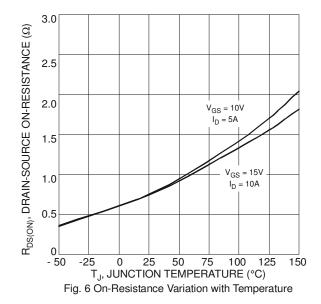


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature







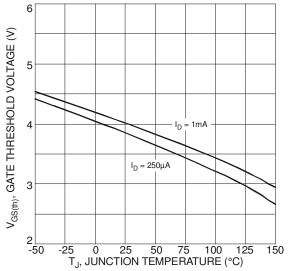
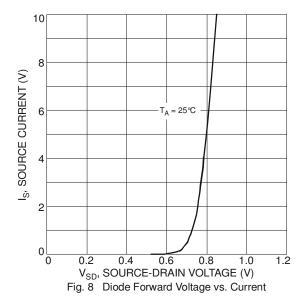
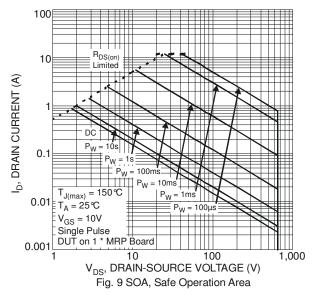
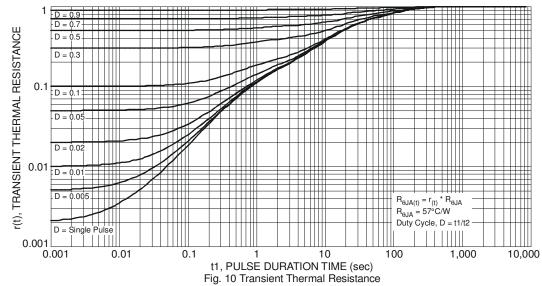


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





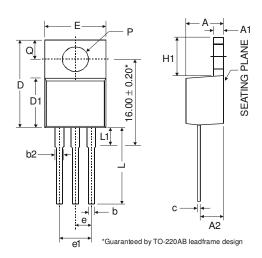






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TO220AB					
Dim	Min	Тур	Max		
Α	3.56	1	4.82		
A 1	0.51	1	1.39		
A2	2.04	•	2.92		
b	0.39	0.81	1.01		
b2	1.15	1.24	1.77		
С	0.356	-	0.61		
D	14.22	1	16.51		
D1	8.39	1	9.01		
е	2.54				
e1	5.08				
Ε	9.66	1	10.66		
H1	5.85	1	6.85		
L	12.70	ı	14.73		
L1	-	-	6.35		
Р	3.54	-	4.08		
Q	2.54	-	3.42		
All Dimensions in mm					

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